

DMTH6005LPSQ

60V +175°C N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI5060-8

Product Summary

BV _{DSS}	R _{DS(ON)} max	I _D T _C = +25°C (Note 10)
60V	$5.5 \text{m}\Omega$ @ $V_{GS} = 10V$	100A

Description and Applications

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

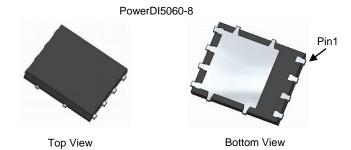
- High Frequency Switching
- Sync. Rectification
- **DCDC** Converters

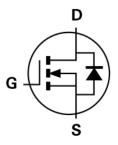
Features

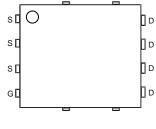
- Rated to +175°C Ideal for High Ambient Temperature **Environments**
- 100% Unclamped Inductive Switching ensures more reliable and robust end application
- Low $R_{DS(ON)}$ minimizes power losses
- $\begin{tabular}{ll} Low Q_g minimizes switching losses \\ \begin{tabular}{ll} Lead-Free Finish; RoHS Compliant (Notes 1 & 2) \\ \end{tabular}$
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

Mechanical Data

- Case: PowerDI[®]5060-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.097 grams (Approximate)







Internal Schematic

Top View Pin Configuration

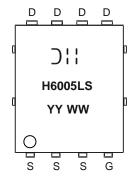
Ordering Information (Note 5)

Part Number	Case	Packaging
DMTH6005LPSQ-13	PowerDI5060-8	2,500 / Tape & Reel

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Please refer to https://www.diodes.com/quality/.
- 5. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

Marking Information



) | = Manufacturer's Marking H6005LS = Product Type Marking Code YYWW = Date Code Marking YY = Year (ex: 18 = 2018)WW = Week (01 to 53)

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Maximum Ratings ($@T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage		V _{DSS}	60	V
Gate-Source Voltage		V _{GSS}	±20	V
Continuous Drain Current (Note 6)	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I _D	20.6 17.2	А
Continuous Drain Current (Note 7)	$T_{C} = +25^{\circ}C$ (Note 10) $T_{C} = +100^{\circ}C$	I _D	100 90	А
Maximum Continuous Body Diode Forward Current (Note 7)	Is	100	Α	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)		I _{DM}	160	Α
Avalanche Current, L = 1mH		I _{AS}	14.8	Α
Avalanche Energy, L = 1mH		Eas	98	mJ

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 6)	$T_A = +25^{\circ}C$	P_{D}	3.2	W
Thermal Resistance, Junction to Ambient (Note 6)		$R_{\theta JA}$	47	°C/W
Total Power Dissipation (Note 7)	$T_C = +25^{\circ}C$	P _D	150	W
Thermal Resistance, Junction to Case (Note 7)		R _{0JC}	1	°C/W
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +175	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

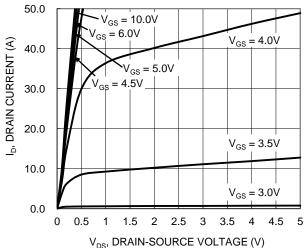
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)				•		•	
Drain-Source Breakdown Voltage	BV _{DSS}	60	_	_	V	$V_{GS} = 0V$, $I_D = 1mA$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1	μA	$V_{DS} = 48V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)			•	•		•	
Gate Threshold Voltage	V _{GS(TH)}	1	_	3	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
		_	4.4	5.5	mΩ	$V_{GS} = 10V, I_D = 50A$	
Static Drain-Source On-Resistance	R _{DS(ON)}	_	5.7	7.2		$V_{GS} = 6V, I_D = 20A$	
	, ,	_	7.7	10		$V_{GS} = 4.5V, I_D = 12.5A$	
Diode Forward Voltage	V _{SD}	_	0.9	_	V	$V_{GS} = 0V, I_{S} = 50A$	
DYNAMIC CHARACTERISTICS (Note 9)	<u> </u>					•	
Input Capacitance	C _{iss}	_	2962	_		.,	
Output Capacitance	Coss	_	965.2	_	pF	$V_{DS} = 30V, V_{GS} = 0V,$ f = 1MHz	
Reverse Transfer Capacitance	C _{rss}	_	59.8	_		I = IIVII IZ	
Gate Resistance	Rq	_	0.66	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = 10V)	Qg	_	47.1	_			
Total Gate Charge (V _{GS} = 4.5V)	Qq	_	23.1	_	1		
Gate-Source Charge	Q _{gs}		10.2	_	nC	$V_{DD} = 30V, I_{D} = 50A$	
Gate-Drain Charge	Q_{gd}	_	12.5	_			
Turn-On Delay Time	t _{D(ON)}		8.3	_			
Turn-On Rise Time	t _R		9.4	_		$V_{DD} = 30V, V_{GS} = 10V,$	
Turn-Off Delay Time	t _{D(OFF)}		22	_	ns	$I_D = 30A, R_G = 3.3\Omega$	
Turn-Off Fall Time	t _F		8.9	_			
Body Diode Reverse Recovery Time	t _{RR}		40.4	_	ns		
Body Diode Reverse Recovery Charge	Q _{RR}	_	49.7	_	nC	$I_F = 30A$, di/dt = 100A/ μ s	

Notes:

- 6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
 7. Thermal resistance from junction to soldering point (on the exposed drain pad).
 8. Short duration pulse test used to minimize self-heating effect.
 9. Guaranteed by design. Not subject to product testing.
 10. Package limited.

DMTH6005LPSQ





V_{DS}, DRAIN-SOURCE VOLTAGE (V) Figure 1. Typical Output Characteristic

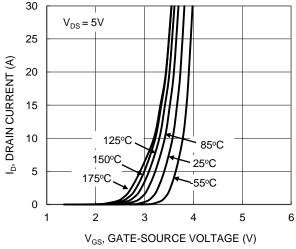


Figure 2. Typical Transfer Characteristic

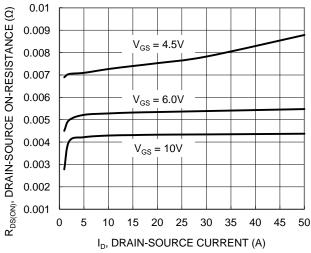


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

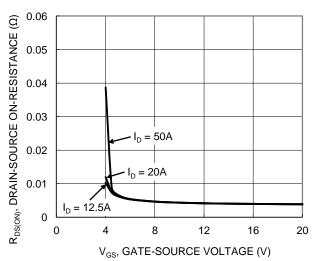


Figure 4. Typical Transfer Characteristic

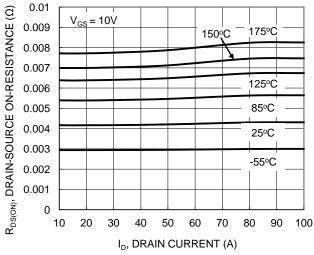


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

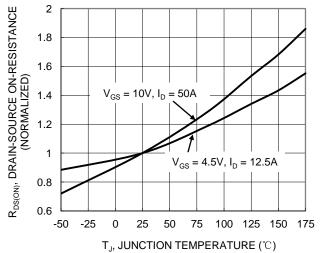


Figure 6. On-Resistance Variation with Junction Temperature

DMTH6005LPSQ



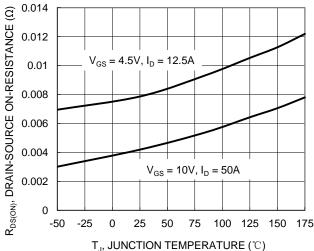
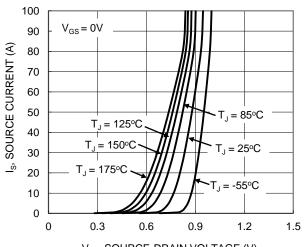


Figure 7. On-Resistance Variation with Junction Temperature



V_{SD}, SOURCE-DRAIN VOLTAGE (V) Figure 9. Diode Forward Voltage vs. Current

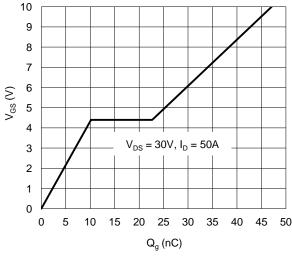


Figure 11. Gate Charge

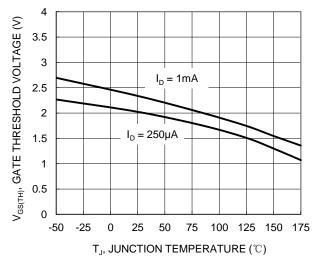
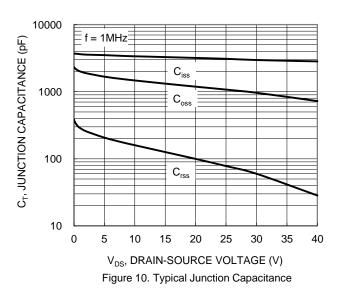


Figure 8. Gate Threshold Variation vs. Junction Temperature



1000 R_{DS(ON)} Limited 100 ID, DRAIN CURRENT (A) 10 1 T_{J(Max)} = 175°C T_C = 25°C Single Pulse 0.1 **DUT** on Infinite Heatsink $V_{GS} = 10V$ 0.01 0.1 10 100 V_{DS}, DRAIN-SOURCE VOLTAGE (V) Figure 12. SOA, Safe Operation Area



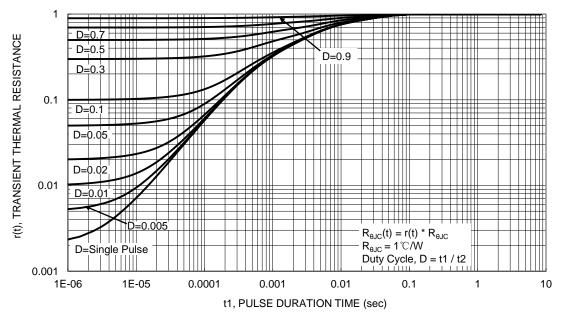


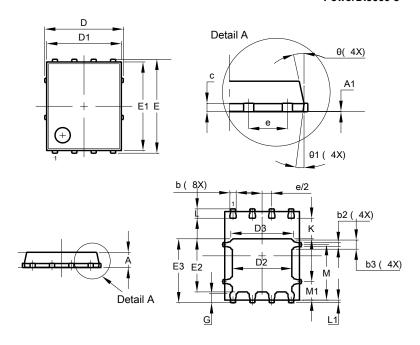
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8

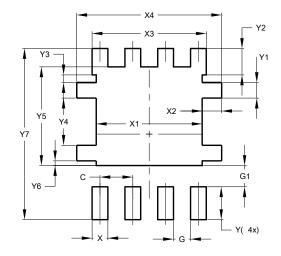


PowerDI5060-8					
Dim	Min	Тур			
Α	0.90	1.10	1.00		
A1	0.00	0.05	-		
b	0.33	0.51	0.41		
b2	0.200	0.350	0.273		
b3	0.40	0.80	0.60		
С	0.230	0.330	0.277		
D	;	5.15 BSC			
D1	4.70	5.10	4.90		
D2	3.70	4.10	3.90		
D3	3.90				
Е	6.15 BSC				
E1	5.60	6.00	5.80		
E2	3.28	3.68	3.48		
E3	3.99				
е	1.27 BSC				
G	0.51	0.71	0.61		
K	0.51	-	-		
L	0.51	0.71	0.61		
L1	0.100	0.200	0.175		
М	3.235	4.035	3.635		
M1	1.00	1.40	1.21		
Θ	10°	12°	11°		
Θ1	6°	8°	7°		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8



Dimensions	Value (in mm)			
С	1.270			
G	0.660			
G1	0.820			
Х	0.610			
X1	4.100			
X2	0.755			
Х3	4.420			
X4	5.610			
Υ	1.270			
Y1	0.600			
Y2	1.020			
Y3	0.295			
Y4	1.825			
Y5	3.810			
Y6	0.180			
Y7	6.610			



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